National Semiconductor

54/74ETL16245 16-Bit Data Transceiver with Incident Wave Switching

General Description

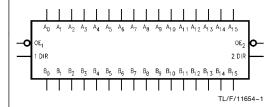
The 54/74ETL16245 contains sixteen non-inverting bidirectional buffers with TRI-STATE® outputs designed with incident wave switching, live insertion support and enhanced noise margin for TTL backplane applications.

Both the A and B ports include a bus hold circuit to latch the output to the value last forced on that pin.

The B port of this device includes 25Ω series output resistors, which minimize undershoot and ringing.

Features

- Supports the VME64 ETL specification
- Functionally and pin compatible with industry standard TTL 16245 SSOP pinout
- Logic Symbol



Pin Description

Pin Names	Description
DIR	Transmit/Receive Input
ŌĒ	Output Enable Input (Active LOW)
An	Backplane Bus Data
B _n	Local Bus Data

Improved TTL-compatible input threshold range

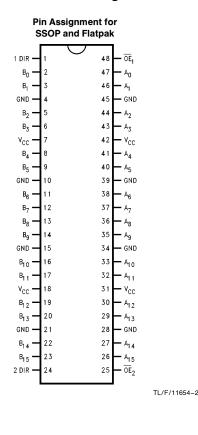
- \blacksquare High drive TTL-compatible outputs (I_{OH}=-60 mA, I_{OL}=90 mA)
- \blacksquare Supports 25 $\!\Omega$ incident wave switching on the A port
- BiCMOS design significantly reduces power dissipation.

PRELIMINARY

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- \blacksquare Distributed V_{CC} and GND pin configuration minimizes high-speed switching noise
- 25Ω series-dampening resistor on B-port
- Available in 48-pin SSOP and ceramic flatpak
- Guaranteed output skew
- Guaranteed simultaneous switching noise level and dynamic threshold performance
- Guaranteed latchup protection

Connection Diagram



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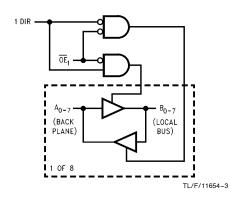
RRD-B30M105/Printed in U. S. A.

Functional Description

The device uses byte-wide Direction (DIR) control and Output Enable (\overline{OE}) controls. The DIR inputs determine the direction of data flow through the device. The \overline{OE} inputs disable the A and the B ports.

The part contains active circuitry which keeps all outputs disabled when V_{CC} is less than 2.2V to aid in live insertion applications.

Logic Diagrams (Positive Logic)

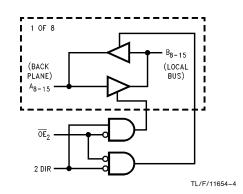


ETL's Improved Noise Immunity

TTL input thresholds are typically determined by temperature-dependent junction voltages which result in worst case input thresholds between 0.8V and 2.0V. By contrast, ETL provides greater noise immunity because its input thresholds are determined by current mode input circuits similar to those used for ECL or BTL. ETL's worst case input thresholds, between 1.4V and 1.6V, are compensated for temperature, voltage and process variations.

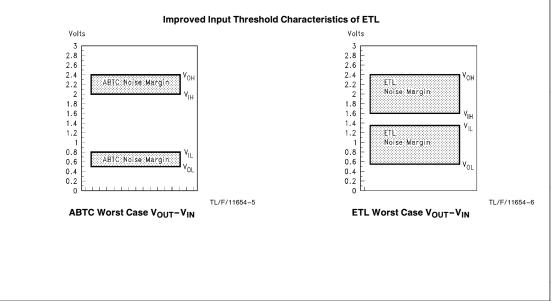
Truth Table (Each 8-bit Section)

Inp	outs	Operation
ŌĒ	DIR	operation
L	L	A Data to B Bus
L	Н	B Data to A Bus
н	х	Isolation
Н	X	Isolation



Incident Wave Switching

When TTL logic is used to drive fully loaded backplanes, the combination of low backplane bus characteristic impedance, wide TTL input threshold range and limited TTL drive generally require multiple waveform reflections before a valid signal can be received across the backplane. The VME International Trade Association (VITA) defined ETL to provide incident wave switching which increases the data transfer rate of a VME backplane and extends the life of VME applications. TTL compatibility with existing VME backplanes and modules was maintained.

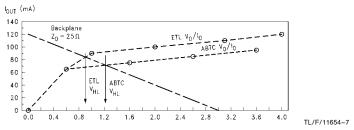


Incident Wave Switching (Continued)

To demonstrate the incident wave switching capability, consider a VME application. A VME bus must be terminated to $+\,2.94V$ with $190\,\Omega$ at each end of its 21 card backplane. The surge impedance presented by a fully loaded VME backplane is approximately 25Ω . If the output voltage/current of an ABTC driver is plotted with this load, the inter-

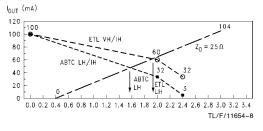
section at 1.2V for a falling edge and at 1.6V for a rising edge does not reach the worst case input threshold of a second ABTC circuit. This is shown in the two figures below. However, an ETL driver located at one end of the backplane is able to provide incident wave switching because it has a higher drive and a tighter input threshold.

Estimated ETL/ABTC Initial Falling Edge Step

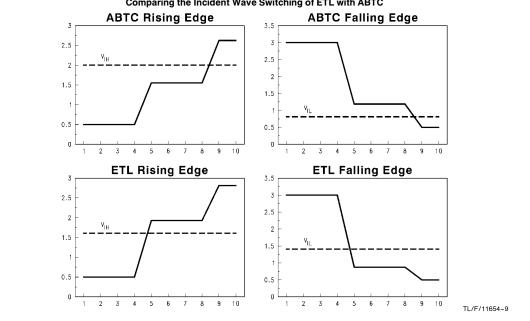


Because ETL has a much more precise input threshold region, an ETL receiver will interpret its predicted falling input of 0.85V as a logic ZERO and the initial rising edge of 1.9V as a logic ONE. This comparison is for the case of a 25Ω surge impedance backplane driven from one end.

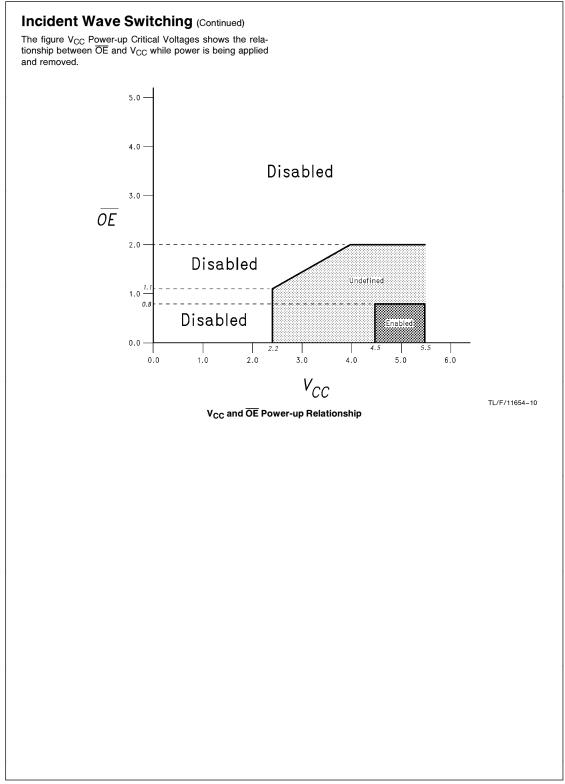
Estimated ETL/ABTC Initial Rising Edge Step



The resulting ABTC and ETL waveform predictions and their input thresholds are compared below. This shows how ETL can achieve backplane speeds not always possible with conventional TTL compatible logic families.



Comparing the Incident Wave Switching of ETL with ABTC



Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	-65°C to +150°C
Ambient Temperature under Bias	-55°C to +125°C
Junction Temperature under Bias Ceramic Plastic	−55°C to +175°C −55°C to +150°C
V _{CC} Pin Potential to Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to $+7.0V$
Input Current (Note 2)	-50 mA to $+5.0$ mA
Voltage Applied to Any Output in the Disabled or	
Power-off State	-0.5V to 5.5V
in the HIGH State	-0.5V to V _{CC}
Current Applied to Output in LOW State (Max)	128 mA

DC Latchup Source Current Over Voltage Latchup (I/O) -500 mA 10V

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature Military Commercial	−55°C to +125°C −40°C to +85°C
Supply Voltage Military Commercial	+4.5V to +5.5V +4.5V to +5.5V
Minimum Input Edge Rate Data Input Enable Input	(Δt/ΔV) 20 ns/V 50 ns/V

DC Electrical Characteristics

Symbol	Parameter			ETL1624	15	Units	v	Conditions	
Symbol	Parameter		Min	Тур	Мах	Units	Vcc	Conditions	
VIH	Input HIGH Voltage	ŌĒ	2.0			V		Recognized HIGH Signal	
		Other Inputs	1.6			v			
VIL	Input LOW Voltage	ŌĒ			0.8	v		Recognized LOW Signal	
		Other Inputs			1.4	v			
V _{CD}	Input Clamp Diode Voltage				-1.2	V	Min	$I_{IN} = -18 \text{ mA} (\overline{OE}_n, \text{DIR})$	
V _{OH}	Output HIGH Voltage	B Port	2.4 2.0		V _{CC} - 1	V V V	Min	$I_{OH} = -100 \ \mu A$ $I_{OH} = -1 \ m A$ $I_{OH} = -12 \ m A$	
		A Port	2.4 2.0		V _{CC} – 1	V V V	Min	$I_{OH} = -1 \text{ mA}$ $I_{OH} = -32 \text{ mA}$ $I_{OH} = -60 \text{ mA}$	
V _{OL}	Output LOW Voltage	B Port			0.4 0.8	V V	Min	$I_{OL} = 1 \text{ mA}$ $I_{OL} = 12 \text{ mA}$	
		A Port			0.55 0.9	V V	Min	$I_{OL} = 64 \text{ mA}$ $I_{OL} = 90 \text{ mA}$	
HOLD	Bus Hold Current	A Port,	100			μA	Min	$\overline{\text{OE}}$ = HIGH, V _O = 0.8V	
		B Port	-100			μΛ		$\overline{\text{OE}}$ = HIGH, V _O = 2.0V	
I _{OFF}	Output Current, Power Down				100	μΑ	0.0	$\begin{array}{l} V_{CC} \text{Bias} = \text{0V} \\ V_{I} \text{or} V_{O} \leq 4.5 \text{V} \end{array}$	
l _l	Input Current Control Pins	54ETL			±10	μΑ	5.5	$V_{IN} = 0 \text{ or } V_{CC}$	
		74ETL			±5	μΑ	5.5	$V_{IN} = 0 \text{ or } V_{CC}$	
I _{IH} + I _{OZH}	Output Leakage Current				50	μΑ	5.5	$V_{OUT} = 2.7V, \overline{OE} = 2.0V$	
I _{IL} + I _{OZL}	Output Leakage Current				-50	μΑ	5.5	$V_{OUT} = 0.5V, \overline{OE} = 2.0V$	

Symbol	Parameter		ETL16245	5	Units	V	Conditions
Symbol	Parameter	Min	Тур	Мах	Units	V _{CC}	Conditions
ICCH	Power Supply Current			40	mA	Max	All Outputs HIGH, $\overline{OE} = LOW$, DIR = HIGH or LOV
I _{CCL}	Power Supply Current			80	mA	Max	All Outputs LOW, $\overline{OE} = LOW$, DIR = HIGH or LOV
I _{CCZ}	Power Supply Current			40	mA	Max	\overline{OE} = HIGH All Others at V _{CC} or GND DIR = HIGH or LOW
ICCD	Dynamic I _{CC} No Load (Note 1)			0.15	mA/ MHz	Max	Outputs Open $\overline{OE}_n = GND$, DIR = HIGH One Bit Toggling, 50% Duty Cycl
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}			1.0	v	5.0	$T_A = 25^{\circ}C \text{ (Note 2)}$ $C_L = 50 \text{ pF; } R_L = 500\Omega$
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-1.4			v	5.0	$T_A = 25^{\circ}C \text{ (Note 2)}$ $C_L = 50 \text{ pF; } R_L = 500\Omega$
V _{OHV}	Minimum High Level Dynamic Output Voltage (Note 1)		2.7		v	5.0	$\begin{array}{l} T_A = 25^\circ C \text{ (Note 4)} \\ C_L = 50 \ pF; R_L = 500 \Omega \end{array}$
V _{IHD}	Minimum High Level Dynamic Input Voltage (Note 1)	2.0	1.5		v	5.0	$T_A = 25^{\circ}C \text{ (Note 3)}$ $C_L = 50 \text{ pF; } R_L = 500\Omega$
V _{ILD}	Maximum Low Level Dynamic Input Voltage (Note 1)		1.2	0.8	v	5.0	$T_A = 25^{\circ}C$ (Note 3) $C_L = 50 \text{ pF; } R_L = 500\Omega$

Note 1: Guaranteed, but not tested.

Note 2: Max. number of outputs defined as (n). n - 1 data inputs are driven 0V to 3V. One output at LOW. Guaranteed, but not tested.

Note 3: Max. number of data inputs (n) switching. n - 1 inputs switching 0V to 3V. Input-under-test switching: 3V to threshold (V_{ILD}), 0V to threshold (V_{ILD}). Guaranteed, but not tested.

Note 4: Max. number of outputs defined as (n). n - 1 data inputs are driven 0V to 3V. One output HIGH. Guaranteed, but not tested.

AC Electrical Characteristics

		74ETL		54ETL $T_{A} = -55^{\circ}C \text{ to } + 125^{\circ}C$ $V_{CC} = 4.5V - 5.5V$		74	ETL			
Symbol	Symbol Parameter		$\begin{array}{l} \textbf{T_A}=\ +\ \textbf{25^{\circ}C}\\ \textbf{V_{CC}}=\ +\ \textbf{5V} \end{array}$					Units	Fig. No.	
		Min	Тур	Max	Min	Мах	Min	Мах		
t _{PLH} t _{PHL}	Propagation Delay A _n to B _n	1.5 1.5		7.0 7.0			1.5 1.5	7.0 7.0	ns	1, 2, 4
t _{PLH} t _{PHL}	Propagation Delay B _n to A _n	1.5 1.5		7.0 7.0			1.5 1.5	7.0 7.0	ns	1, 2, 4
t _{PZH} t _{PZL}	Output Enable Time	1.0 1.0		7.0 7.0			1.0 1.0	7.0 7.0	ns	1, 2, 3
t _{PHZ} t _{PLZ}	Output Disable Time	1.0 1.0		7.0 7.0			1.0 1.0	7.0 7.0	ns	1, 2, 3
t _r	Rise Time 1V \rightarrow 2V, A _n Outputs	1.2		3.0			1.2	3.0	ns	1, 2, 4
t _f	Fall Time 2V \rightarrow 1V, A _n Outputs	1.2		3.0			1.2	3.0	ns	1, 2, 4

Skew						
		$74ETL$ $T_{\Delta} = -40^{\circ}C \text{ to } +85^{\circ}C$	$54ETL$ $T_{\blacktriangle} = -55^{\circ}C \text{ to } + 125^{\circ}C$			
Symbol	Parameter	$V_{CC} = 4.5V - 5.5V$ 16 Outputs Switching	$V_{CC} = 4.5V - 5.5V$ 16 Outputs Switching	Units	Conditions	
		Max	Max			
t _{OHS} (Notes 1, 2)	Pin-to-Pin Skew LH/HL An to Bn	1.3		ns	Figures 1, 2, 4	
^t онs (Notes 1, 2)	Pin-to-Pin Skew LH/HL Bn to An	1.3		ns	Figures 1, 2, 4	
t _{PS} (Notes 1, 2)	Duty Cycle Skew Bn to An	2.0		ns	Figures 1, 2, 4	
t _{PS} (Notes 1, 2)	Duty Cycle Skew An to Bn	2.0		ns	Figures 1, 2, 4	

VME Extended Skew

		74ETL	54ETL			
Symbol	Parameter	$ \begin{array}{l} {\sf T}_{\sf A}=\ -40^\circ {\sf C} \ to \ +85^\circ {\sf C} \\ {\sf V}_{\sf CC}=\ 4.5 {\sf V}-5.5 {\sf V} \\ 16 \ {\sf Outputs} \ {\sf Switching} \end{array} $	$\label{eq:TA} \begin{split} \textbf{T}_{\textbf{A}} &= -55^{\circ}\textbf{C} \text{ to } + 125^{\circ}\textbf{C} \\ \textbf{V}_{\textbf{CC}} &= 4.5\textbf{V} - 5.5\textbf{V} \\ \textbf{16 Outputs Switching} \end{split}$	Units	Conditions	
		Max	Мах			
t _{PV} (Notes 1, 2)	Device-to-Device Skew LH/HL Transitions Bn to An	4.0		ns	Figures 1, 2, 4	
t _{CP} (Notes 1, 2)	Device-to-Device Skew LH/HL Transitions An to Bn	2.5		ns	Figures 1, 2, 4	
t _{CP} (Note 1, 3)	Change in Propagation Delay with Load Bn to An	4.0		ns	Figures 1, 2, 4	
t _{CPV} (Notes 1, 2, 3)	Device-to-Device, Change in Propagation Delay with with Load Bn to An	6.0		ns	Figures 1, 2, 4	

Note 1: Skew is defined as the absolute difference in delay between two outputs. The specification applies to any outputs switching HIGH to LOW, LOW to HIGH, or any combination switching HIGH-to-LOW or LOW-to-HIGH. This specification is guaranteed but not tested.

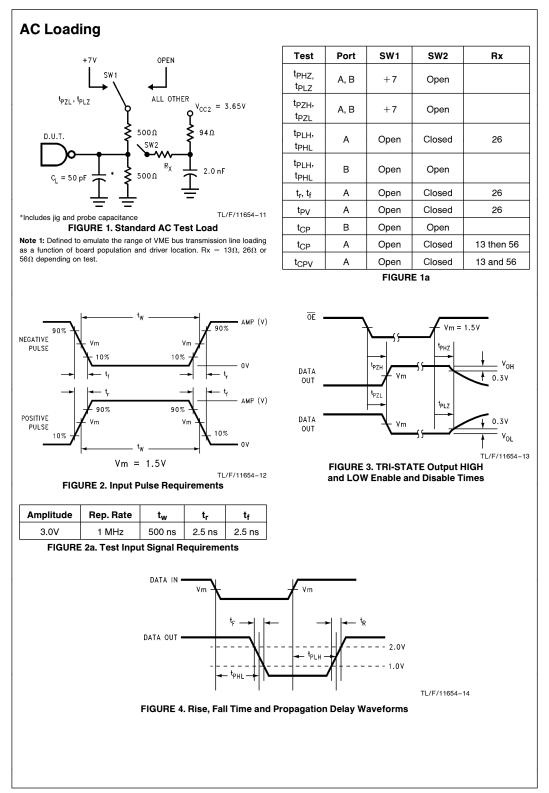
Note 2: This is measured with both devices at the same value of V_{CC} \pm 1% and with package temperature differences of 20°C from each other.

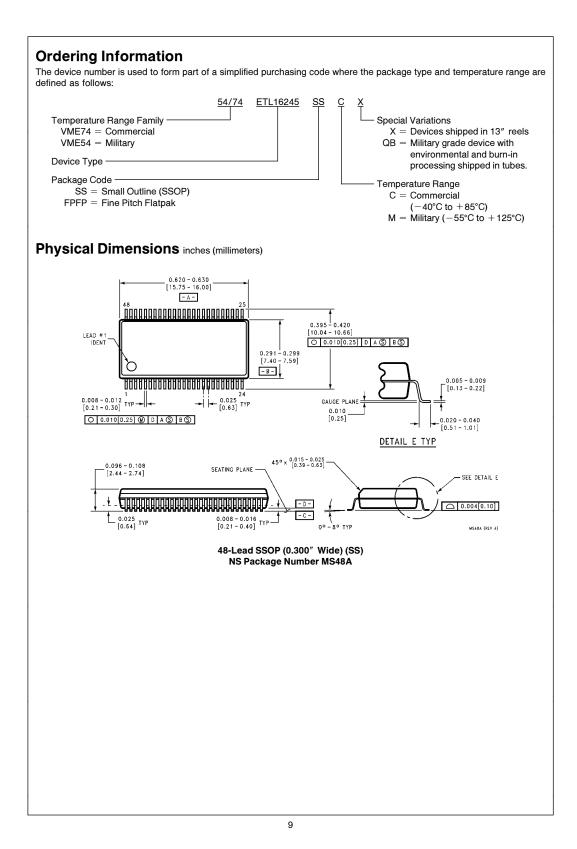
Note 3: This is measured with Rx in Figure 1 at 13Ω for one unit and at 56Ω for the other unit.

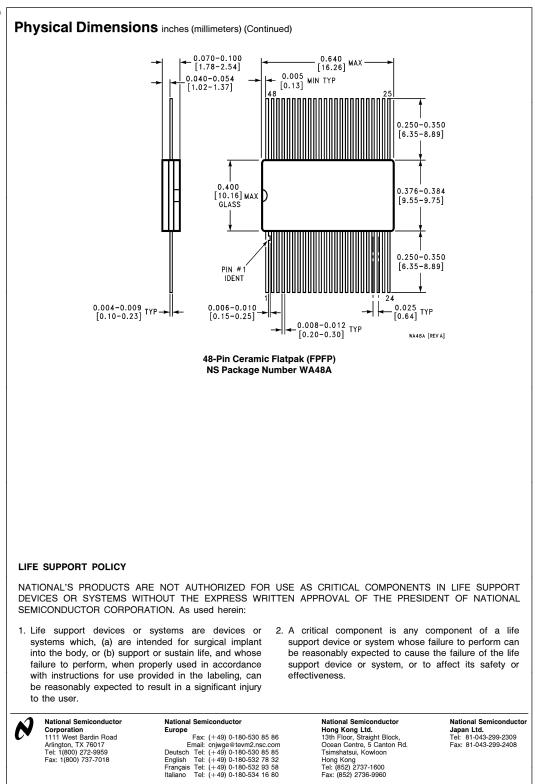
Capacitance

Symbol	Parameter	Тур	Мах	Units	Conditions, $T_A = 25^{\circ}C$
C _{IN}	Input Capacitance	5	8	pF	$V_{CC} = 0.0V (\overline{OE}_n, DIR)$
CI/O (Note 1)	Output Capacitance	9	12	pF	$V_{CC} = 5.0V (A_{n})$

Note 1: $C_{I/O}$ is measured at frequency f = 1 MHz, per MIL-STD-883B, Method 3012.







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